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Kind regards,

Team Nexperia

# PEMD20; PUMD20

# NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$

Rev. 01 — 2 May 2005

**Product data sheet** 

## 1. Product profile

#### 1.1 General description

NPN/PNP Resistor-Equipped Transistors (RET).

Table 1: Product overview

Type number	Package I		PNP/PNP	NPN/NPN
	Philips	JEITA	complement	complement
PEMD20	SOT666	-	PEMB20	PEMH20
PUMD20	SOT363	SC-88	PUMB20	PUMH20

#### 1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

#### 1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

#### 1.4 Quick reference data

Table 2: Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	50	V
I <sub>O</sub>	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



## 2. Pinning information

Table 3: Pinning

Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa143

## 3. Ordering information

**Table 4: Ordering information** 

Type number	Package		
	Name	Description	Version
PEMD20	-	plastic surface mounted package; 6 leads	SOT666
PUMD20	SC-88	plastic surface mounted package; 6 leads	SOT363

## 4. Marking

Table 5: Marking codes

Type number	Marking code [1]
PEMD20	6H
PUMD20	T6*

[1] \* = -: made in Hong Kong

\* = p: made in Hong Kong

\* = t: made in Malaysia

\* = W: made in China

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## 5. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor; for the PNP transistor	with negative pola	rity		
$V_{CBO}$	collector-base voltage	open emitter	-	50	V
$V_{CEO}$	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	10	V
VI	input voltage TR1				
	positive		-	+12	V
	negative		-	-10	V
	input voltage TR2				
	positive		-	+10	V
	negative		-	-12	V
Io	output current (DC)		-	100	mA
I <sub>CM</sub>	peak collector current		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363		<u>[1]</u> -	200	mW
	SOT666		[1][2] -	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
Per device					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363		[1] -	300	mW
	SOT666		[1][2]	300	mW

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



## 6. Thermal characteristics

**Table 7: Thermal characteristics** 

Parameter stor	Conditions	Min	Тур	Max	Unit
stor					
thermal resistance from junction to ambient	in free air				
SOT363		<u>[1]</u> _	-	625	K/W
SOT666		[1][2] _	-	625	K/W
thermal resistance from junction to ambient	in free air				
SOT363		<u>[1]</u> -	-	416	K/W
SOT666		[1] [2]	-	416	K/W
	junction to ambient SOT363 SOT666  thermal resistance from junction to ambient SOT363	junction to ambient  SOT363  SOT666  thermal resistance from in free air junction to ambient  SOT363	junction to ambient  SOT363  SOT666  11 -  thermal resistance from in free air junction to ambient  SOT363  11 -	junction to ambient  SOT363  SOT666  112  thermal resistance from in free air junction to ambient  SOT363  11	junction to ambient  SOT363  [1] 625  SOT666  [1][2] 625  thermal resistance from in free air junction to ambient  SOT363  [1] 416

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

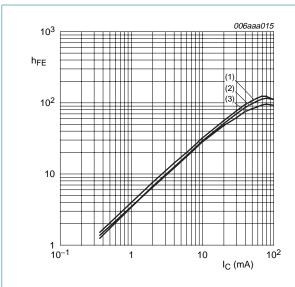
## 7. Characteristics

**Table 8: Characteristics** 

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	sistor; for the PNP tran	nsistor with negative polari	ty			
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_E = 0 \text{ A}$	-	-	100	nA
I <sub>CEO</sub>	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μΑ
	cut-off current	$V_{CE} = 30 \text{ V; } I_{B} = 0 \text{ A;}$ $T_{j} = 150 \text{ °C}$	-	-	50	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_C = 0 \text{ A}$	-	-	2	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 20 \text{ mA}$	30	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_C = 1 \text{ mA}$	-	1.2	0.5	V
$V_{I(on)}$	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	2	1.6	-	V
R1	bias resistor 1 (input)		1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		8.0	1	1.2	
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz				
	TR1 (NPN)		-	-	2.5	pF
	TR2 (PNP)		-	-	3	pF

<sup>[2]</sup> Reflow soldering is the only recommended soldering method.



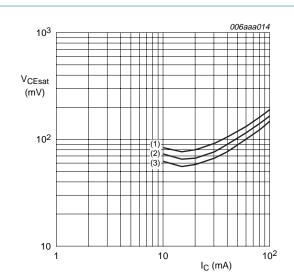
$$V_{CE} = 5 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 1. TR1 (NPN): DC current gain as a function of collector current; typical values



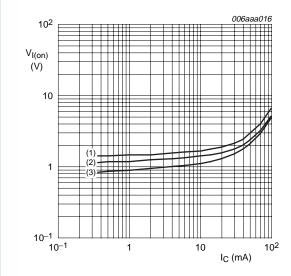
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = 100 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 2. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



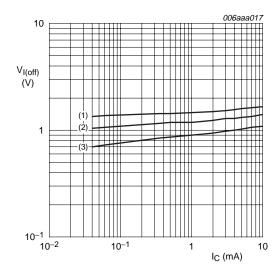


(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 3. TR1 (NPN): On-state input voltage as a function of collector current; typical values



$$V_{CE} = 5 V$$

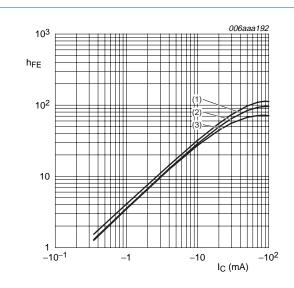
(1) 
$$T_{amb} = -40 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 4. TR1 (NPN): Off-state input voltage as a function of collector current; typical values

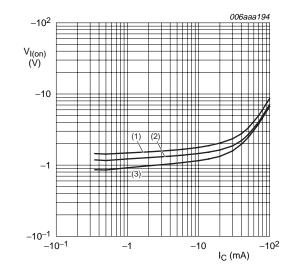
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$$V_{CE} = -5 \text{ V}$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

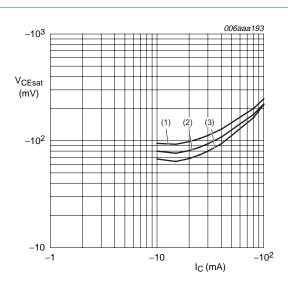
Fig 5. TR2 (PNP): DC current gain as a function of collector current; typical values



$$V_{CE} = -0.3 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

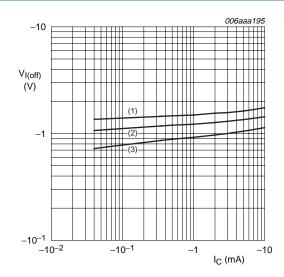
Fig 7. TR2 (PNP): On-state input voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B}=20$$

- (1)  $T_{amb} = 100 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = -40 \, ^{\circ}C$

Fig 6. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

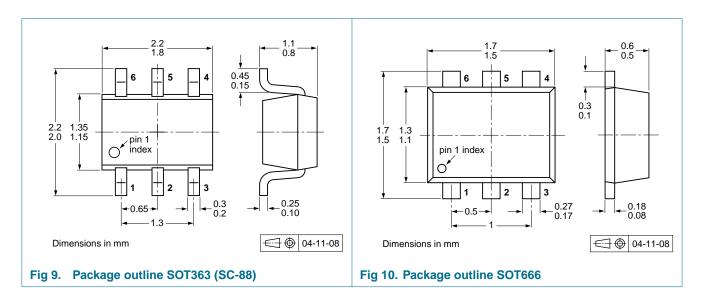


$$V_{CE} = -5 \text{ V}$$

- (1)  $T_{amb} = -40 \, ^{\circ}C$
- (2)  $T_{amb} = 25 \, ^{\circ}C$
- (3)  $T_{amb} = 100 \, ^{\circ}C$

Fig 8. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

## 8. Package outline



## 9. Packing information

Table 9: Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code. [1]

Type number Package		Description		Packing quantity			
				3000	4000	8000	10000
PEMD20	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
	4 mm pitch, 8 mm tape and reel		-	-115	-	-	
PUMD20	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165

<sup>[1]</sup> For further information and the availability of packing methods, see <u>Section 15</u>.

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<sup>[2]</sup> T1: normal taping

<sup>[3]</sup> T2: reverse taping







#### Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
PEMD20_PUMD20_1	20050502	Product data sheet	-	9397 750 14419	-



Level	Data sheet status [1]	Product status [2] [3]	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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## **Philips Semiconductors**

## PEMD20; PUMD20

NPN/PNP resistor-equipped transistors; R1 = 2.2 k $\Omega$ , R2 = 2.2 k $\Omega$ 

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